

Si6426DQ

20V N-Channel PowerTrench® MOSFET

General Description

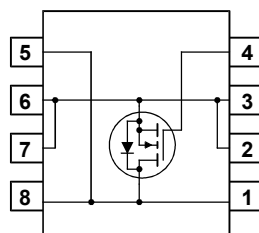
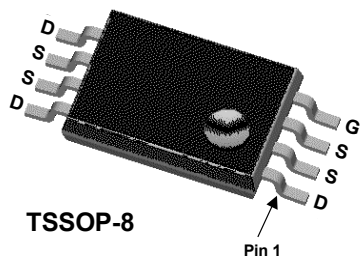
This N-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (2.5V to 8V).

Applications

- Battery protection
- DC/DC conversion
- Power management
- Load switch

Features

- 5.4 A, 20 V $R_{DS(ON)} = 35\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
 $R_{DS(ON)} = 40\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
- Extended V_{GSS} range ($\pm 8\text{V}$) for battery applications
- High performance trench technology for extremely low $R_{DS(ON)}$
- Low profile TSSOP-8 package



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|--|-----------------|------------------|
| V_{DSS} | Drain-Source Voltage | 20 | V |
| V_{GSS} | Gate-Source Voltage | ± 8 | V |
| I_D | Drain Current – Continuous (Note 1) | 5.4 | A |
| | – Pulsed | 30 | |
| P_D | Power Dissipation (Note 1a) (Note 1b) | 1.4 | W |
| | | 1.1 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to $+150$ | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|--|-----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) (Note 1b) | 87 | $^\circ\text{C/W}$ |
| | | 114 | |

Package Marking and Ordering Information

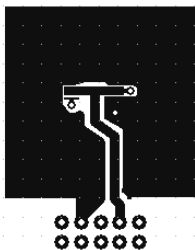
| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|----------|-----------|------------|------------|
| 6426 | Si6426DQ | 13" | 16mm | 3000 units |

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|--|-----|-----|------|----------------------|
| Off Characteristics | | | | | | |
| BV_{DSS} | Drain–Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 20 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C | | 14 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$ | | | 5 | |
| I_{GSSF} | Gate–Body Leakage, Forward | $V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$ | | | 100 | nA |
| I_{GSSR} | Gate–Body Leakage, Reverse | $V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | nA |
| On Characteristics (Note 2) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 0.6 | 0.9 | 1.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$, Referenced to 25°C | | -3 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS} = 4.5\text{ V}, I_D = 5.4\text{ A}$ | | 23 | 35 | m Ω |
| | | $V_{GS} = 2.5\text{ V}, I_D = 4.9\text{ A}$ | | 33 | 40 | |
| $I_{D(on)}$ | On–State Drain Current | $V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$ | 20 | | | A |
| | | $V_{GS} = 2.5\text{ V}, V_{DS} = 5\text{ V}$ | 8 | | | |
| g_{FS} | Forward Transconductance | $V_{DS} = 10\text{ V}, I_D = 5.4\text{ A}$ | | 11 | | S |
| Dynamic Characteristics | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 710 | | pF |
| C_{oss} | Output Capacitance | | | 173 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 84 | | pF |
| Switching Characteristics (Note 2) | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD} = 6\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$ | | 7 | 14 | ns |
| t_r | Turn–On Rise Time | | | 17 | 31 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | | 16 | 29 | ns |
| t_f | Turn–Off Fall Time | | | 3 | 6 | ns |
| t_{rr} | Reverse Recovery Time | $V_{GS} = 0\text{ V}, I_F = 1.5\text{ A},$ $di_F/dt = 100\text{ A}/\mu\text{s}$ | | 14 | 100 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 6\text{ V}, I_D = 5.4\text{ A},$ $V_{GS} = 4.5\text{ V}$ | | 7 | 10 | nC |
| Q_{gs} | Gate–Source Charge | | | 1.5 | | nC |
| Q_{gd} | Gate–Drain Charge | | | 1.2 | | nC |
| Drain–Source Diode Characteristics and Maximum Ratings | | | | | | |
| I_S | Maximum Continuous Drain–Source Diode Forward Current | | | | 1.25 | A |
| V_{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 1.25\text{ A}$ (Note 2) | | 0.7 | 1.2 | V |

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



- a) $87^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper.



- b) $114^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

- c) Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Typical Characteristics

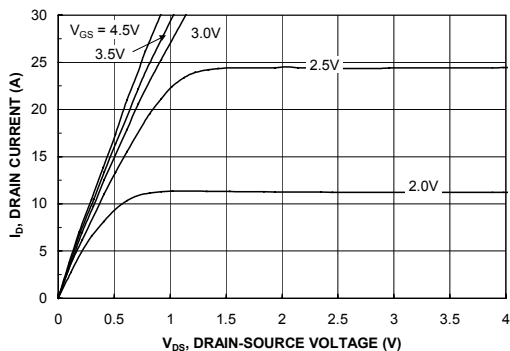


Figure 1. On-Region Characteristics.

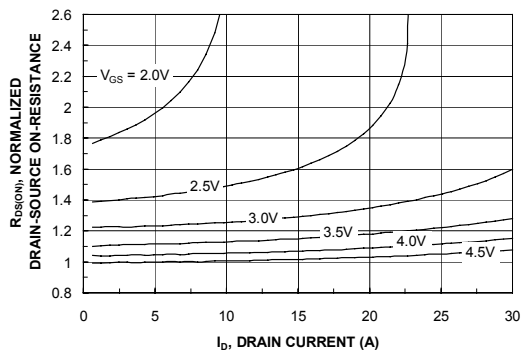


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

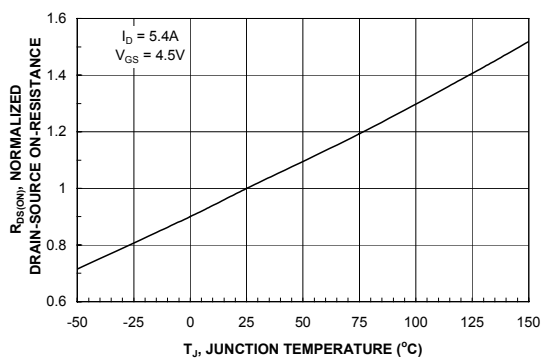


Figure 3. On-Resistance Variation with Temperature.

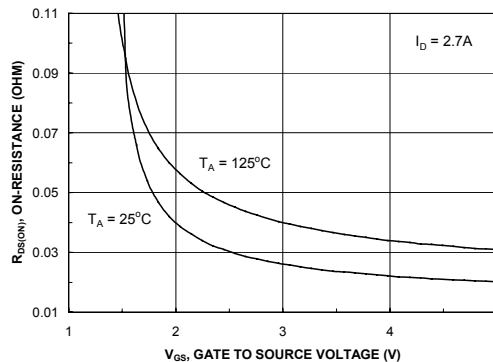


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

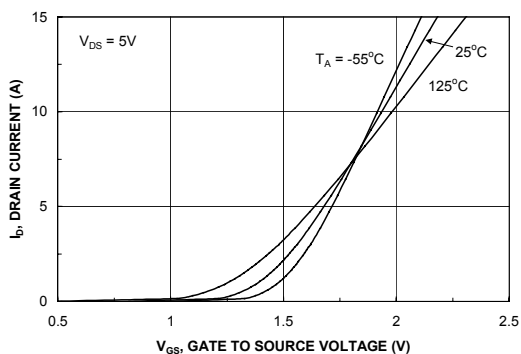


Figure 5. Transfer Characteristics.

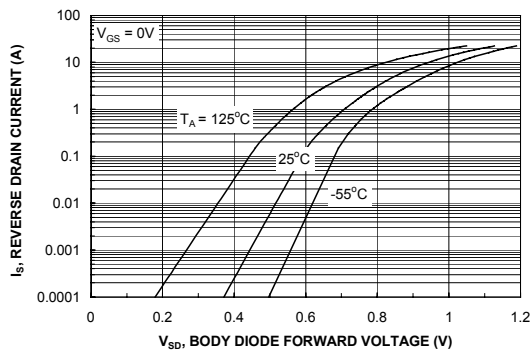


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

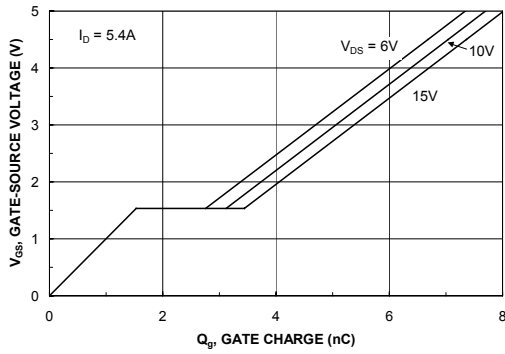


Figure 7. Gate Charge Characteristics.

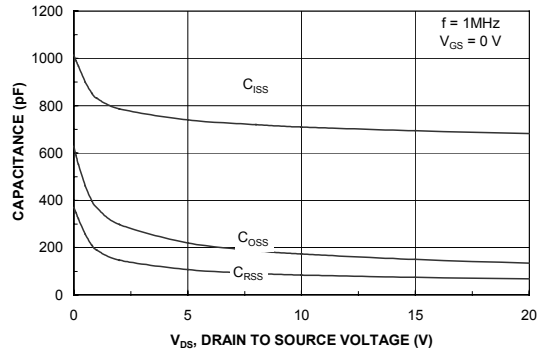


Figure 8. Capacitance Characteristics.

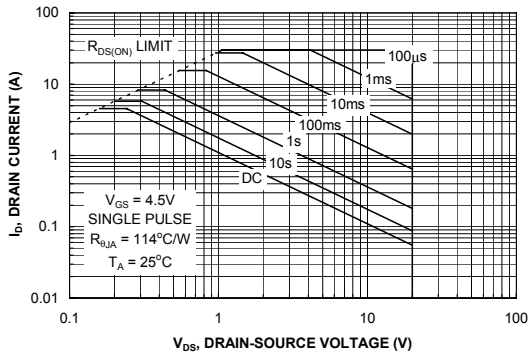


Figure 9. Maximum Safe Operating Area.

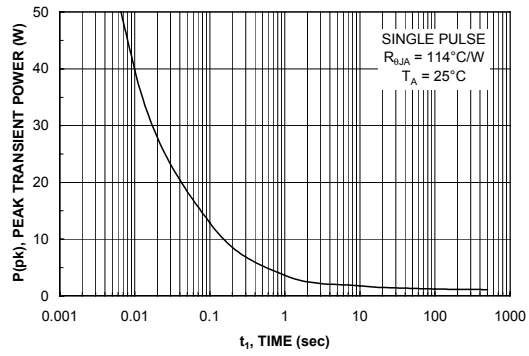


Figure 10. Single Pulse Maximum Power Dissipation.

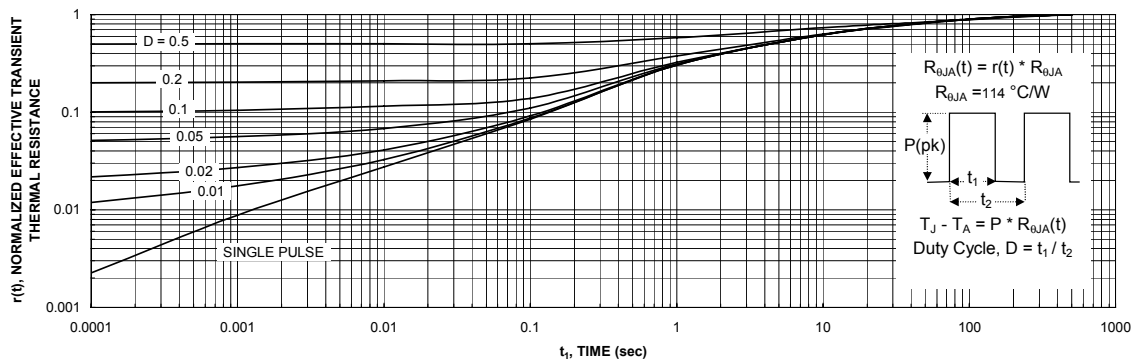


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

| | | | | |
|-----------------------------------|----------------------------------|----------------------------------|------------------------------|-------------------|
| ACE _x TM | FAST [®] | OPTOLOGIC TM | SMART START TM | VCX TM |
| Bottomless TM | FAST _r TM | OPTOPLANAR TM | STAR*POWER TM | |
| CoolFET TM | FRFET TM | PACMAN TM | Stealth TM | |
| CROSSVOLT TM | GlobalOptoisolator TM | POPT TM | SuperSOT TM -3 | |
| DenseTrench TM | GTO TM | Power247 TM | SuperSOT TM -6 | |
| DOMET TM | HiSeC TM | PowerTrench [®] | SuperSOT TM -8 | |
| EcoSPARK TM | ISOPLANAR TM | QFET TM | SyncFET TM | |
| E ² CMOS TM | LittleFET TM | QST TM | TinyLogic TM | |
| EnSigna TM | MicroFET TM | QT Optoelectronics TM | TruTranslation TM | |
| FACT TM | MicroPak TM | Quiet Series TM | UHC TM | |
| FACT Quiet Series TM | MICROWIRE TM | SILENT SWITCHER [®] | UltraFET [®] | |

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|------------------------|---|
| Advance Information | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice. |
| Preliminary | First Production | This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| No Identification Needed | Full Production | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| Obsolete | Not In Production | This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only. |